



TAYCHIPST Surface Mount Trench MOS Barrier Schottky Rectifier

VSSB420S

200V 4.0A

FEATURES

- Low profile package
- Ideal for automated placement
- Trench MOS Schottky technology
- Low power losses, high efficiency
- Low forward voltage drop
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Mechanical Data

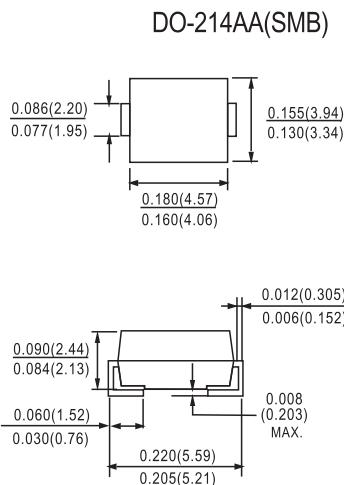
Case: DO-214AA (SMB)

Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: Color band denotes the cathode end



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	VSSB420S		UNIT	
Device marking code		V4D			
Maximum repetitive peak reverse voltage	V_{RRM}	200		V	
Maximum DC forward current	$I_F^{(1)}$	4.0		A	
	$I_F^{(2)}$	1.8			
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	I_{FSM}	40		A	
Voltage rate of change (rated V_R)	dV/dt	10 000		V/ μ s	
Operating junction and storage temperature range	T_J, T_{STG}	- 40 to + 150		°C	

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	TEST CONDITIONS	SYMBOL	TYP.	MAX.	UNIT	
Instantaneous forward voltage	$I_F = 4.0 \text{ A}$	$V_F^{(1)}$	1.44	1.90	V	
			0.71	0.80		
Reverse current per diode	$V_R = 180 \text{ V}$	$I_R^{(2)}$	3	-	μA	
			0.7	-	mA	
	$V_R = 200 \text{ V}$		4	150	μA	
			1.1	10	mA	
Typical junction capacitance	4.0 V, 1 MHz	C_J	120	-	pF	

THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	VSSB420S		UNIT	
Typical thermal resistance	$R_{\theta JA}^{(1)}$	120		$^\circ\text{C}/\text{W}$	
	$R_{\theta JM}^{(2)}$	15			

Notes

(1) Free air, mounted on recommended PCB 1 oz. pad area; thermal resistance $R_{\theta JA}$ - junction to ambient

(2) Units mounted on PCB with 20 mm x 20 mm copper pad areas; thermal resistance $R_{\theta JM}$ - junction to mount



TAYCHIPST

Surface Mount Trench MOS Barrier Schottky Rectifier

VSSB420S

200V 4.0A

RATINGS AND CHARACTERISTIC CURVES

VSSB420S

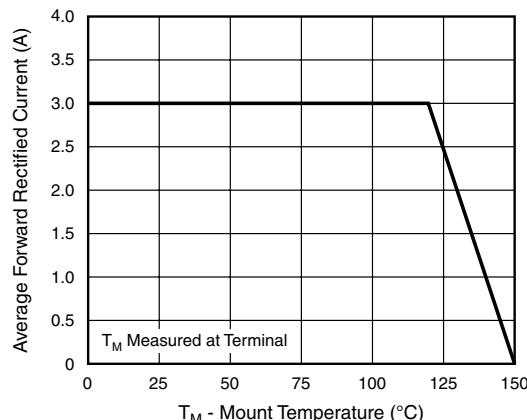


Fig. 1 - Maximum Forward Current Derating Curve

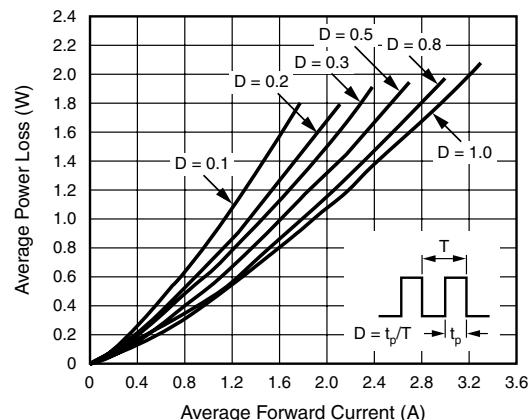


Fig. 2 - Forward Power Loss Characteristics

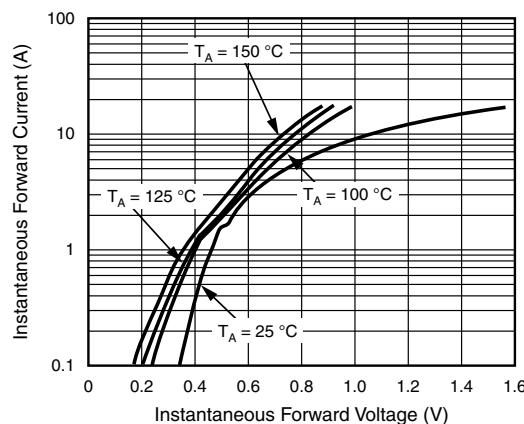


Fig. 3 - Typical Instantaneous Forward Characteristics

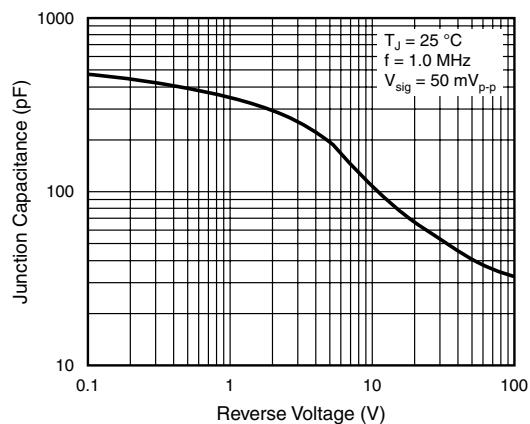


Fig. 5 - Typical Junction Capacitance

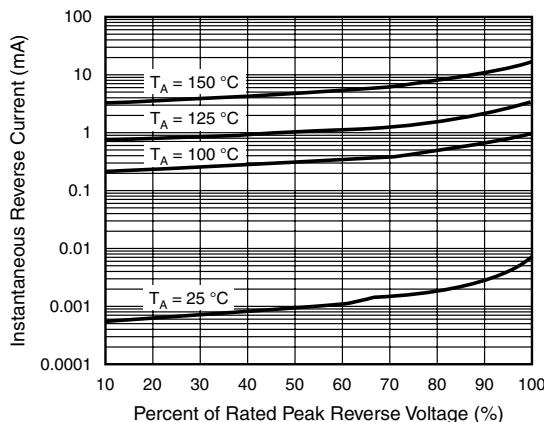


Fig. 4 - Typical Reverse Characteristics

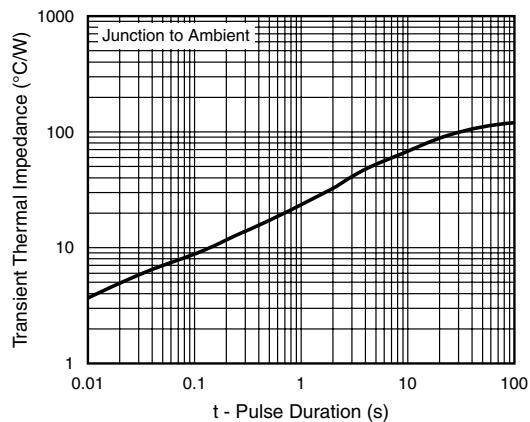


Fig. 6 - Typical Transient Thermal Impedance